

Search Hist. 3/7/5 3/7/5 (7pp)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	light adj extraction adj layer and nitride.ti,ab,clm. and (257/79.cc1s. 257/8\$1.cc1s. 257/9\$1.cc1s. 257/100.cc1s. 257/101.cc1s. 257/102.cc1s. 257/103.cc1s.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 07:05
L2	3	light adj extraction adj (film layer) and nitride.ti,ab,clm. and (257/79.cc1s. 257/8\$1.cc1s. 257/9\$1.cc1s. 257/100.cc1s. 257/101.cc1s. 257/102.cc1s. 257/103.cc1s.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 07:06
L4	145	light adj extraction near4 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 07:15
L5	72	light adj extraction near4 substrate and "257"/\$2.cc1s.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 07:15
L6	78	light adj extraction near4 substrate and (257/10\$1.cc1s. "257"/\$2.cc1s.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:16
L7	55	light adj extraction near4 substrate and (257/10\$1.cc1s. "257"/\$2.cc1s.) and nitride and (sapphire "Al.sub.2"\$1"O.sub.3")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:18
L8	0	light adj extraction adj (layer film) near4 substrate and (257/10\$1.cc1s. "257"/\$2.cc1s.) and nitride and (sapphire "Al.sub.2"\$1"O.sub.3")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:19
L9	46	light adj extraction near4 substrate and (257/10\$1.cc1s. "257"/\$2.cc1s.) and nitride and (sapphire "Al.sub.2"\$1"O.sub.3") and (epitaxial epitaxially epi)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:33
L10	32	light adj extraction near4 substrate and (257/10\$1.cc1s. "257"/\$2.cc1s.) and nitride and (sapphire "Al.sub.2"\$1"O.sub.3") and (epitaxial epitaxially epi) and refractive adj index	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:35

L11	2	light adj extraction near4 substrate and (257/10\$1.ccls. "257"/\$2.ccls.) and nitride and (sapphire "Al.sub.2"\$1"O.sub.3") and (epitaxial epitaxially epi) and refractive adj index near4 extraction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:38
L12	13	light adj extraction near4 substrate and (257/10\$1.ccls. "257"/\$2.ccls.) and nitride and (sapphire "Al.sub.2"\$1"O.sub.3") and (epitaxial epitaxially epi) and refractive adj index near8 (extract extraction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:39
L13	13	light adj extraction near4 substrate and (257/10\$1.ccls. "257"/\$2.ccls.) and nitride and (sapphire "Al.sub.2"\$1"O.sub.3") and (epitaxial epitaxially epi) and refractive adj index near8 (extract extraction) and (ITO ZnO ZnS MgO ZnSe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:46
L14	0	match\$3 near4 refractive adj index near4 substrate and (257/10\$1.ccls. "257"/\$2.ccls.) and nitride and (sapphire "Al.sub.2"\$1"O.sub.3") and (epitaxial epitaxially epi) and refractive adj index near8 (extract extraction) and (ITO ZnO ZnS MgO ZnSe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:47
L15	0	match\$3 near8 refractive adj index near8 substrate and (257/10\$1.ccls. "257"/\$2.ccls.) and nitride and (sapphire "Al.sub.2"\$1"O.sub.3") and (epitaxial epitaxially epi) and refractive adj index near8 (extract extraction) and (ITO ZnO ZnS MgO ZnSe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:48
L16	0	anti-reflective adj layer near4 substrate and (257/10\$1.ccls. "257"/\$2.ccls.) and nitride and (sapphire "Al.sub.2"\$1"O.sub.3") and (epitaxial epitaxially epi) and refractive adj index near8 (extract extraction) and (ITO ZnO ZnS MgO ZnSe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:48

L17	0	antireflective adj layer near4 substrate and (257/10\$1.ccls. "257"/\$2.ccls.) and nitride and (sapphire "Al.sub.2"\$1'O.sub.3") and (epitaxial epitaxially epi) and refractive adj index near8 (extract extraction) and (ITO ZnO ZnS MgO ZnSe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:49
L18	0	antireflective adj layer near4 substrate and (257/10\$1.ccls. "257"/\$2.ccls.) and nitride and (sapphire "Al sub.2"\$1'O.sub.3") and (epitaxial epitaxially epi) and (ITO ZnO ZnS MgO ZnSe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:49
L19	0	antireflective adj (film layer) near4 substrate and (257/10\$1.ccls. "257"/\$2.ccls.) and nitride and (sapphire "Al.sub.2"\$1'O.sub.3") and (epitaxial epitaxially epi) and (ITO ZnO ZnS MgO ZnSe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:49
L20	0	antireflective adj (film layer) near4 substrate and (257/10\$1.ccls. "257"/\$2.ccls.) and nitride and (sapphire "Al.sub.2"\$1'O.sub.3" SiC silicon adj carbide) and (epitaxial epitaxially epi) and (ITO ZnO ZnS MgO ZnSe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:49
L21	0	antireflective adj (film layer) near4 substrate and (257/10\$1.ccls. "257"/\$2.ccls.) and nitride and (sapphire "Al.sub.2"\$1'O.sub.3" SiC silicon adj carbide) and (ITO ZnO ZnS MgO ZnSe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:50
L22	11	antireflective adj (film layer) near4 substrate and nitride and (sapphire "Al.sub.2"\$1'O.sub.3" SiC silicon adj carbide) and (ITO ZnO ZnS MgO ZnSe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:50
L23	63	(anti-reflective antireflective antireflection anti-reflection) adj (film layer) near4 substrate and nitride and (sapphire "Al.sub.2"\$1'O.sub.3" SiC silicon adj carbide) and (ITO ZnO ZnS MgO ZnSe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:51
L24	6	(anti-reflective antireflective antireflection anti-reflection) adj (film layer) near4 substrate and nitride and (sapphire "Al.sub.2"\$1'O.sub.3" SiC silicon adj carbide) and (ITO ZnO ZnS MgO ZnSe) and (epitaxial epitaxy epitaxially)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:52

L25	63	(anti-reflective antireflective antireflection anti-reflection) adj (film layer) near4 substrate and nitride and (sapphire "Al.sub.2" "\$1" O.sub.3" SiC silicon adj carbide) and (ITO ZnO ZnS MgO ZnSe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:52
L26	0	(anti-reflective antireflective antireflection anti-reflection) adj (film layer) near4 substrate and nitride and (sapphire "Al.sub.2" "\$1" O.sub.3" SiC silicon adj carbide) and (ITO ZnO ZnS MgO ZnSe) and (257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:53
L27	0	(anti-reflective antireflective antireflection anti-reflection) adj (film layer) near4 substrate and nitride and (sapphire "Al.sub.2" "\$1" O.sub.3" SiC silicon adj carbide) and (ITO ZnO ZnS MgO ZnSe) and (257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:53
L28	11	(anti-reflective antireflective antireflection anti-reflection) adj (film layer) and nitride and (sapphire "Al.sub.2" "\$1" O.sub.3" SiC silicon adj carbide) and (ITO ZnO ZnS MgO ZnSe) and (257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:58
L29	18	(anti-reflective antireflective antireflection anti-reflection) adj (film layer) and nitride and (sapphire "Al.sub.2" "\$1" O.sub.3" SiC silicon adj carbide) and (257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 08:08
L30	18	(anti-reflective antireflective antireflection anti-reflection) adj (film layer) and nitride and (sapphire "Al.sub.2" "\$1" O.sub.3" SiC silicon adj carbide) and (257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 08:08
L31	28	(anti-reflective antireflective antireflection anti-reflection) adj (film layer) and nitride and (sapphire "Al.sub.2" "\$1" O.sub.3" SiC silicon adj carbide) and (372/4\$1.ccls. 372/50.ccls. 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 08:14

L32	1	(anti-reflective antireflective antireflection anti-reflection) adj (film layer) near8 (sapphire "Al. sub.2"\$1"O.sub.3" SiC silicon adj carbide) and (372/4\$1.ccls. 372/50.ccls. 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.) and nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 08:16
L33	7	(anti-reflective antireflective antireflection anti-reflection) adj (film layer) near4 substrate and (sapphire "Al sub 2'\$1'0.sub.3" SiC silicon adj carbide) and (372/4\$1.ccls. 372/50.ccls. 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.) and nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 08:45
L34	2	("20040113166").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 08:48
L35	112922	34 adn epitax\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 08:48
L36	1	34 and epitax\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 09:05
L37	1	34 and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 09:08
L38	1	34 and substrate near4 (sic silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 09:14
L39	40	"high" near1 thermal adj conductivity near3 substrate and nitride and (buffer binding) adj layer and (light-emitting light adj emitting laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 09:16

L40	30	"high" near1 thermal adj conductivity near3 substrate and nitride and (buffer binding) adj layer and (light-emitting light adj emitting laser) and (sapphire "Al. sub.2"\$1"O.sub.3")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 09:22
L41	23	"high" near1 thermal adj conductivity near3 (layer film) and nitride and (buffer binding) adj layer and (light-emitting light adj emitting laser) and (sapphire "Al. sub.2"\$1"O.sub.3")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 09:23
L42	15	"high" near1 thermal adj conductivity near3 (layer film) and nitride and (buffer binding) adj layer and (light-emitting light adj emitting laser) and (sapphire "Al. sub.2"\$1"O.sub.3") near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 10:12
L43	0	"high" near1 thermal adj conductivity near3 (layer film) and nitride and (buffer binding) adj layer and (light-emitting light adj emitting laser) and (sapphire "Al. sub.2"\$1"O.sub.3") near3 substrate and sacrificial	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 09:23
L44	15	"high" near1 thermal adj conductivity near3 (layer film) and nitride and (buffer binding) adj layer and (light-emitting light adj emitting laser) and (sapphire "Al. sub.2"\$1"O.sub.3" SiC silicon adj carbide) near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 10:51
L45	91930	"high" near1 heat sink and nitride and (buffer binding) adj layer and (light-emitting light adj emitting laser) and (sapphire "Al.sub.2"\$1"O.sub.3" SiC silicon adj carbide) near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 10:21
L46	245	heat adj sink and nitride and (buffer binding) adj layer and (light-emitting light adj emitting laser) and (sapphire "Al.sub.2"\$1"O.sub.3" SiC silicon adj carbide) near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 10:28
L47	4	heat adj sink adj layer and nitride and (buffer binding) adj layer and (light-emitting light adj emitting laser) and (sapphire "Al.sub.2"\$1"O.sub.3" SiC silicon adj carbide) near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 10:29

L48	4	heat adj sink adj layer and nitride and (buffer binding) adj layer and (light-emitting light adj emitting laser) and (sapphire "Al.sub.2"\$1"O.sub.3" SiC silicon adj carbide) near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 10:29
L49	25320	((257/79) or (257/8\$1) or (257/9\$1) or (257/10\$1) or (372/4\$1) or (372/50)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 10:52
L50	0	49 and heat adj sink adj (layer film) and epitax\$5 and nitride and (anti-reflect\$3 light adj extract\$3) and (sapphire sic silicon adj carbide "Al.sub."\$1"O.sub."\$1) near4 substrate and (adhes\$3 buffer binding) adj (layer film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 10:54
S1	11	(("6515306") or ("6420242") or ("6562701") or ("20030033974") or ("20020125485")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 06:53
S2	5	"747934".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/06 15:04
S3	3	light adj extraction adj (layer film) near10 refractive adj index	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/06 15:29
S4	0	light adj extraction adj (layer film) near10 refractive adj index and (SiC silicon adj carbide sapphire "Al.sub.2O.sub.3" corundum) near6 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/06 15:30
S5	1	light adj extraction adj (layer film) near10 refractive adj index and light adj extraction adj layer near10 (ITO indiom adj oxide "In.sub.2O.sub.3" titanium adj oxide zirconium adj oxide zinc adj sulfide zinc adj selenide magnesium adj oxide MgO ZnSe ZnO ZnS "ZrO.sub.2" "TiO.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/06 15:34
S6	0	jp-2001366087\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 15:34